

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This triac is intended for use in motor control circuits where high blocking voltage, high static and dynamic dV/dt as well as high dI_{com}/dt can occur. This "series C0" triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- Isolated mounting base package
- Optimized for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- High voltage capability

3. Applications

- Compressor starting control circuits
- General purpose motor controls
- Reversing induction motor controls e.g. vertical axis washing machines

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 75^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	60	A
		full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 16.7\text{ ms}$	-	-	65	A
T_j	junction temperature		-	-	125	$^\circ\text{C}$
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_2 + G+$; $T_j = 25^\circ\text{C}$; Fig. 7	5	-	35	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	5	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	5	-	35	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	-	50	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.3	1.65	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	1500	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit; Fig. 12	12	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220F (SOT186A)</p>	
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA308X-800C0	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 75 °C; Fig. 1; Fig. 2; Fig. 3	-	8	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; Fig. 4; Fig. 5	-	60	A
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	65	A
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	18	A ² s
dI _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/μs
I _{GM}	peak gate current		-	2	A
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

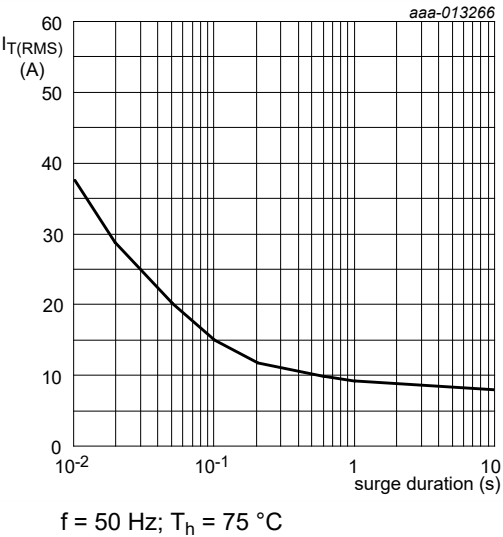


Fig. 1. RMS on-state current as a function of surge duration; maximum values

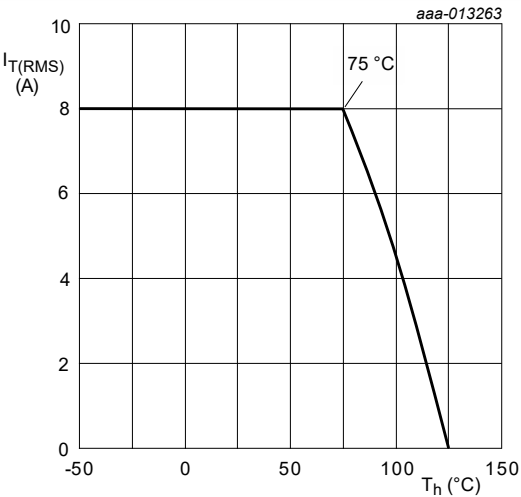


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

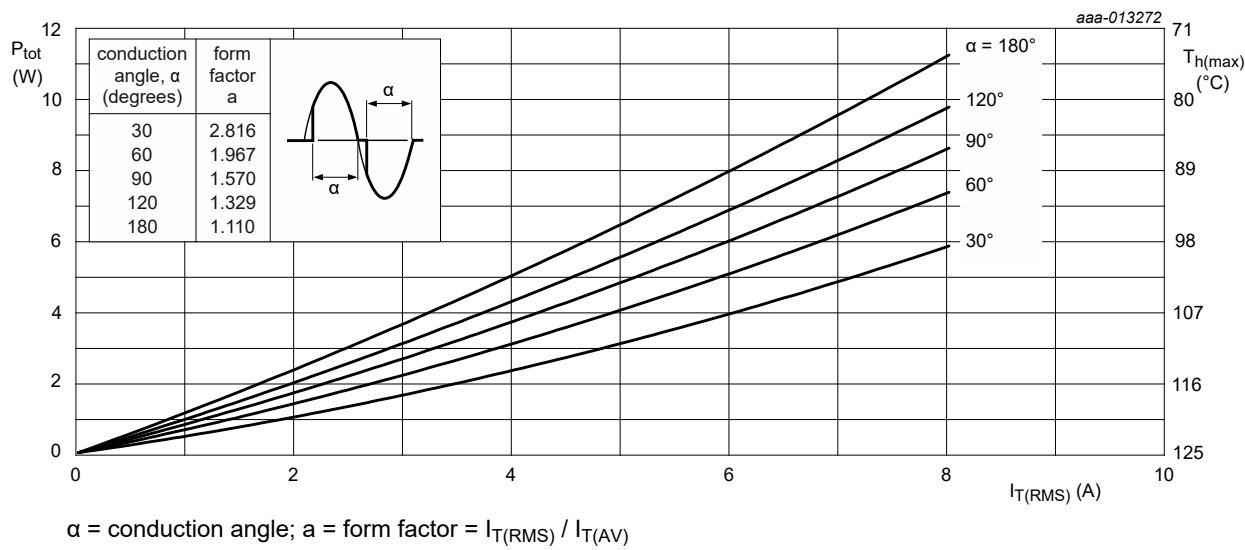


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

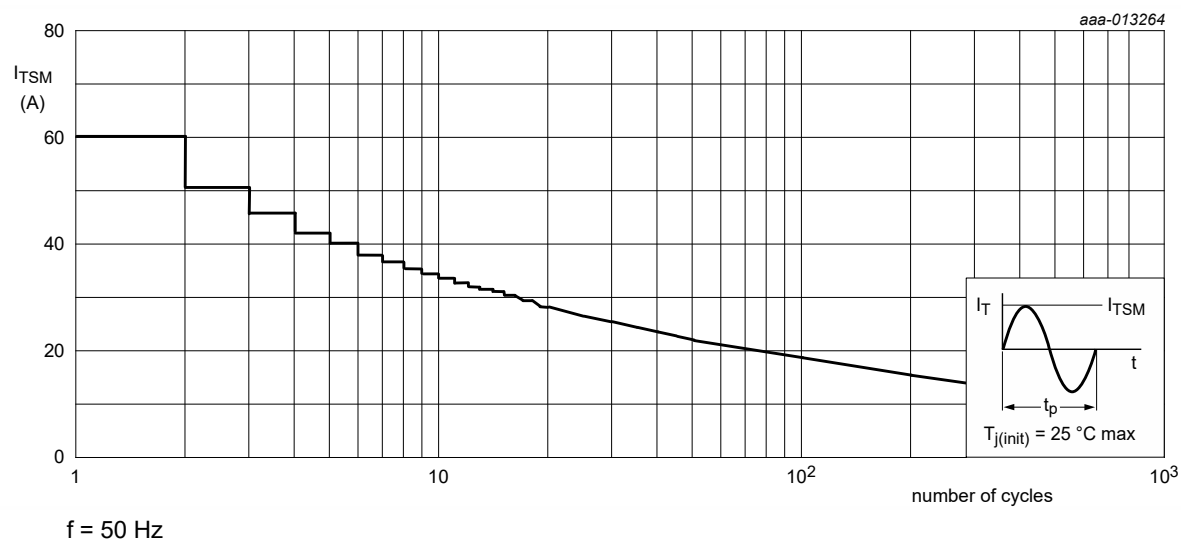
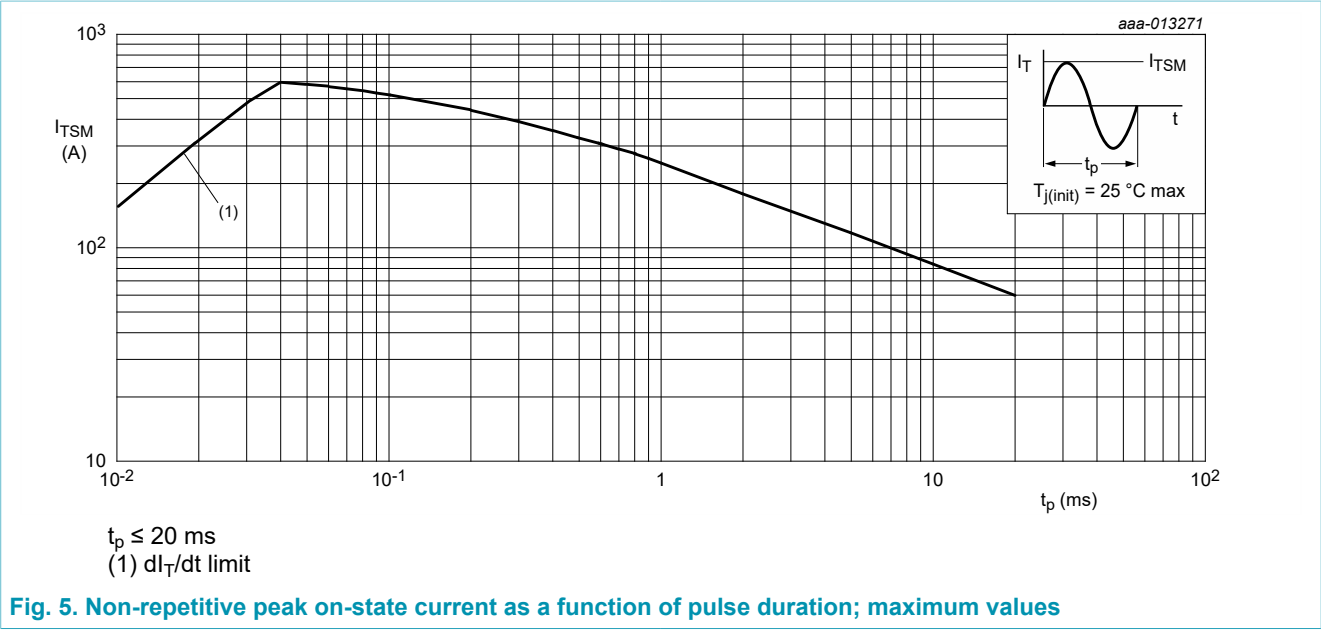


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; Fig. 6	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound	-	-	6.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

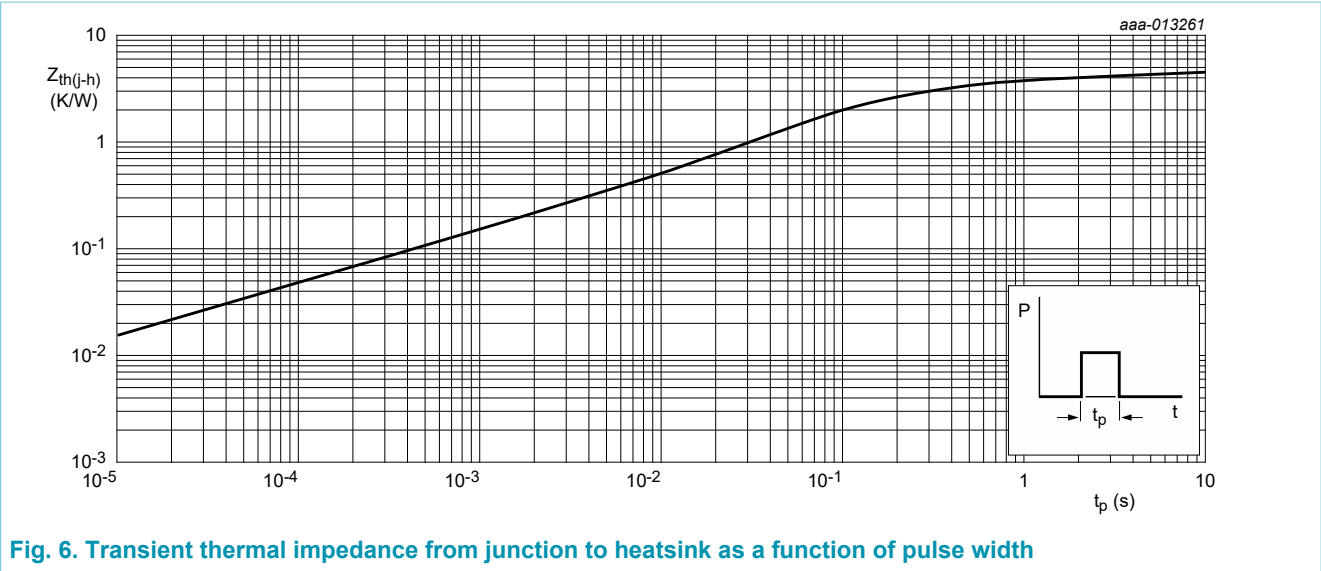


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7		5	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7		5	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7		5	-	35	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8		-	-	50	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8		-	-	75	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8		-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9		-	-	50	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; Fig. 10		-	1.3	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11		-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11		0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C		-	-	10	μA
		V _D = 800 V; T _j = 125 °C		-	-	0.5	mA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		1500	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 8 A; dV _{com} /dt = 20 V/μs; (snubberless condition); gate open circuit; Fig. 12		12	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

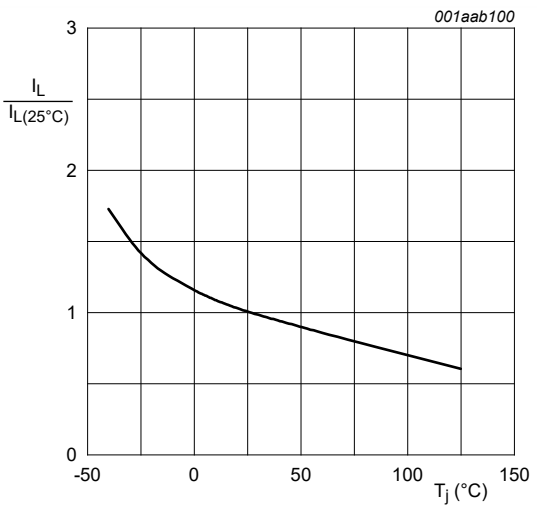
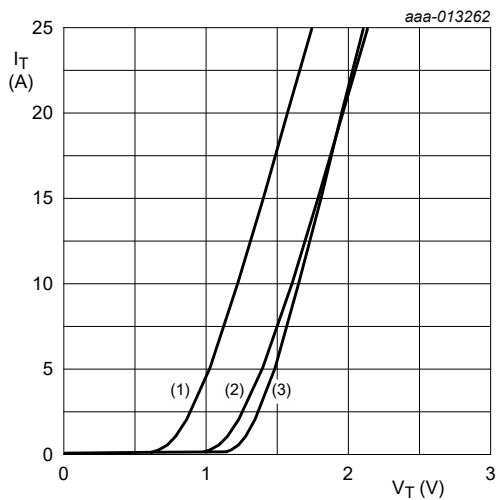


Fig. 8. Normalized latching current as a function of junction temperature

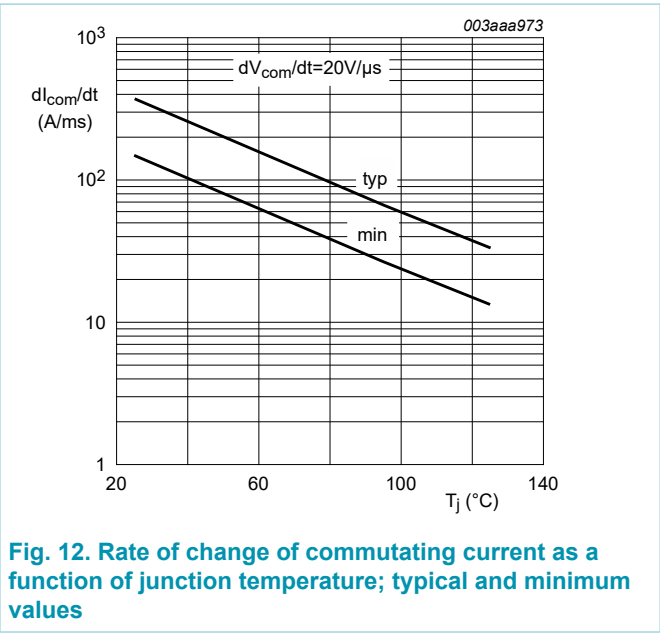
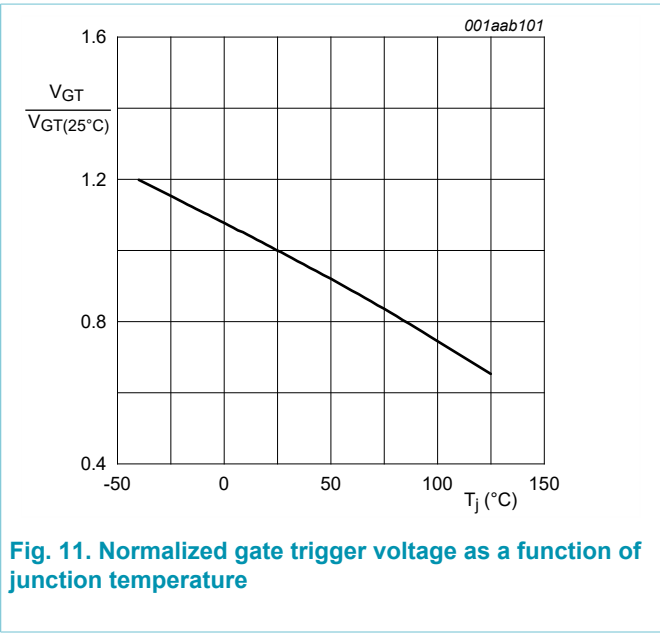


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.205 \text{ V}; R_s = 0.039 \Omega$
- (1) $T_j = 125^{\circ}\text{C}$; typical values
 - (2) $T_j = 125^{\circ}\text{C}$; maximum values
 - (3) $T_j = 25^{\circ}\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage



11. Package outline

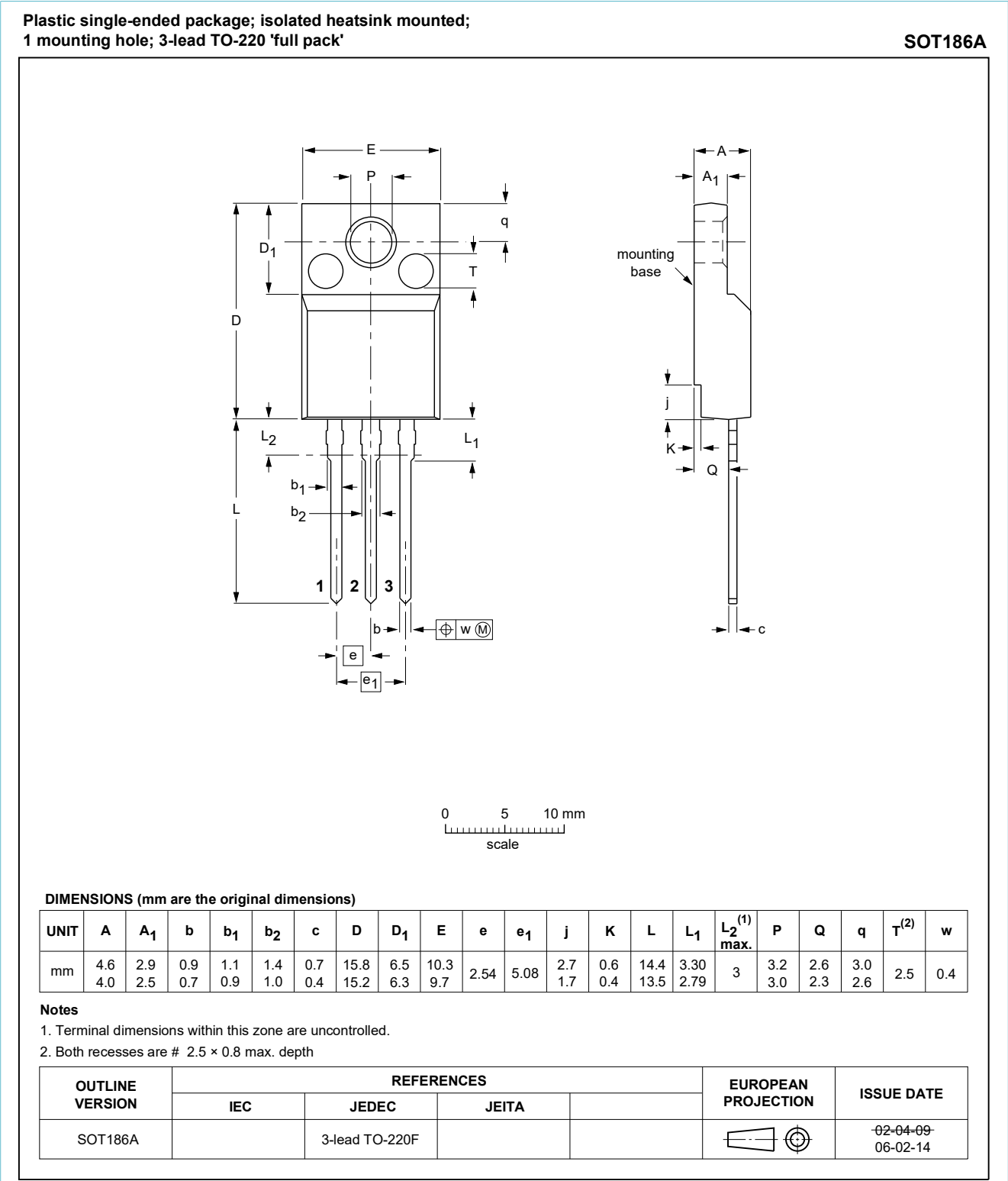


Fig. 13. Package outline TO-220F (SOT186A)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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